	Сотрыете и кложи							
	Application No. 09/652,579							
FEE TRANSMITTAL SHEET (FOR FY 2002)	Filing Date			August 31, 2000				
	First Named Inventor			Vishnu K. Agarwal				
	Group Art Unit			2825				
THAT S. STATE THE		Examiner			Caridad M. Everhart			
		Atty. Docket Number			501082.14 (98-0616.13)			
METHOD OF PAYMENT (CHO) One)	1			EE CALCULATION (Continued)				
1. [X] The Commissioner is hereby authorized to stage any additional fee required under 37 C.F.R. §§ 1.16 and 1.17 and		3. ADDITIONAL FEES						
		intity	Small	*				
1.136(a)(3) and credit any over payments to Deposit Account No.: 50-1266; Deposit Account Name: DORSEY & WHITNEY LLP	Fee Code	Fee (\$)	Fee Code	Fee (\$)	Fee Description	Fee paid		
a IVI objects Frederick	105	130	205	65	Surcharge - Late filing fee or oath	\$		
2. [X] Check Enclosed	127	50	227	25	Surcharge - late provisional filing fee or cover sheet	\$		
FEE CALCULATION	139	130	139	130	Non-English specification	\$		
1. BASIC FILING FEE Large Entity Small Entity	147	2,520	147	2,520	For Filing a Request for Reexamination	\$		
Large Entity Small Entity Fee Fee Fee Fee Fee Description	195	300	196	300	Publication (early or Republication)	\$		
Code (\$) Code (\$)	115	110	215	55	Extension for reply within first month	\$		
101 750 201 375 [] Utility Filing Fee	116	410	216	205	Extension for reply within 2 nd month	 \$		
106 330 206 165 [] Design Filing Fee	117	930	217	465	Extension for reply within 3 rd month Extension for reply within 4 th month	\$		
400 750 200 275 Il Daissus Filing Foo	118 128	1,450 1,970	218 280	725 985	Extension for reply within 5 th month			
108 750 208 375 [] Reissue Filing Fee	120	320	220	160	Filing a brief in support of an appeal	\$		
114 160 214 80 [] Provisional Filing Fee	121	280	270	140	Request for oral hearing	\$		
Subtotal (1) \$0	148	110	248	55	Terminal Disclaimer Fee	\$		
2. EXTRA CLAIM FEES	140	110	240	55	Petition to revive – unavoidable	\$		
Current Claims Prior Extra Fee Fee Paid	141	1,300	241	650	Petition to revive – unintentional	\$		
Total 17 - 20 = 0 x \$ =\$0	142	1,300	242	650	Utility/Reissue issue fee (+ advance copies)	\$		
ind. 2 - 3 = 0 x \$ = \$0	143	470	243	235	Design issue fee (+ advance copies)	\$		
Multiple Dependent Claims x \$ = \$	122	130	122	130	Petitions to the Commissioner	\$		
Subtotal (2)\$0_	123	50	123	50	Petitions related to provisional applications	\$		
Large Entity Small Entity	126	180	126	180	Submission of IDS	\$180		
Fee Fee Fee Fee Fee Description Code (\$) Code (\$)	581	40	81	40	Recording each patent assignment per property (times number of properties)	\$		
103 18 203 9 Claims in excess of 20	179	750	279	375	Request for Continued Examination (RCE)	\$		
102 84 202 42 Independent claims in excess of 3	Other f	ee (spec	ify)		(NOL)	\$		
104 280 204 140 Multiple dependent Claim 109 84 209 42 Reissue independent claims over					Subtotal (3)	\$180		
original patent Reissue claims in excess of 20 and				٦	Total Amount of Payment:	\$180		
over original patent					otal Allount of Faymont.	V 100		
Submitted by:								
Name: Paul F. Rusyn Reg. No.: 42,118					Telephone: (206) 903-8800			
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Signature: Date: Date: Date:								

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PATENT

ce is being deposited with the United States that on the date specified below, this corresponder Patents, Washington, DC 20231. dressed to the

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Vishnu K. Agarwal

Attorney Docket No.: 501082.14 (98-0616.13)

Serial No. : 09/652,579

Group Art Unit

: 2825

Filed

: August 31, 2000

Examiner

: Caridad M. Everhart

Title

: DEVICE AND METHOD FOR PROTECTING AGAINST OXIDATION OF.4

CONDUCTIVE LAYER IN SAID DEVICE

Commissioner of Patents Washington, DC 20231

<u>AMENDMENT</u>

Sir:

Please amend the above-captioned patent application as follows:

In the Claims:

Please cancel claims 47 and 48.

Please amend claims 76, 78, and 79 as follows:

A method of treating a wafer, comprising: (Amended) 76.

depositing a first conductive layer onto the wafer;

exposing the wafe in itu to a reducing environment;

depositing a second conductive layer; and

exposing the wafer to a material selected from the group consisting

of phosphine, HCL, and boron trichloride.

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